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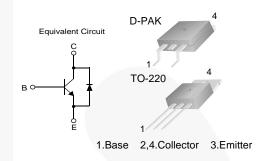


July 2014

KSC5502D / KSC5502DT NPN Triple Diffused Planar Silicon Transistor

Features

- · High Voltage Power Switch Switching Application
- · Wide Safe Operating Area
- · Built-in Free-Wheeling Diode
- Suitable for Electronic Ballast Application
- Small Variance in Storage Time
- Two Package Choices: D-PAK or TO-220



Ordering Information

Part Number	Top Mark	Package	Packing Method		
KSC5502DTM	C5502D	TO-252 3L (DPAK)	Tape and Reel		
KSC5502DTTU	C5502D	TO-220 3L	Rail		

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Value	Unit	
V _{CBO}	Collector-Base Voltage	1200	V	
V _{CEO}	Collector-Emitter Voltage	600	V	
V _{EBO}	Emitter-Base Voltage	12	V	
I _C	Collector Current (DC)	2	Α	
I _{CP}	Collector Current (Pulse) ⁽¹⁾	4	Α	
I _B	Base Current (DC)	1	Α	
I _{BP}	Base Current (Pulse) ⁽¹⁾	2	Α	
T _J	Junction Temperature	150	°C	
T _{STG}	Storage Temperature Range	-65 to 150	°C	
EAS	Avalanche Energy (T _J = 25°C)	2.5	mJ	

Note

1. Pulse test: Pulse width = 5 ms, duty cycle ≤ 10%.

Thermal Characteristics

Values are at $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	KSC5502D (D-PAK)	KSC5502DT (TO-220)	Unit
P _C	Collector Dissipation (T _C = 25°C)	87.83	118.16	W
$R_{\theta JC}$	Thermal Resistance, Junction to Case 1.42 1.06		°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	111.0 62.5 °		°C/W
TL	Maximum Lead Temperature for Soldering Purpose: 1/8 inch from Case for 5 seconds	270		°C

Electrical Characteristics

Values are at $T_C = 25$ °C unless otherwise noted.

Symbol	Parameter	Conditions		Min.	Тур.	Max.	Unit
BV _{CBO}	Collector-Base Breakdown Voltage	$I_C = 1 \text{ mA}, I_E = 0$		1200	1350		V
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C = 5 mA, I _B = 0		600	750		V
BV _{EBO}	Emitter-Base Breakdown Voltage	$I_E = 500 \mu A, I_C = 0$		12.0	13.7		V
	Collector Cut-off Current	V _{CES} = 1200 V, V _{BE} = 0	$T_C = 25^{\circ}C$			100	μΑ
I _{CES}			$T_C = 125^{\circ}C$			500	
1	Collector Cut-off Current	V _{CE} = 600 V, I _B = 0	$T_C = 25^{\circ}C$			100	μΑ
I _{CEO}	Collector Cut-on Current	VCE = 000 V, IB = 0	$T_C = 125^{\circ}C$			500	
I_{EBO}	Emitter Cut-off Current	$V_{EB} = 12 \text{ V}, I_{C} = 0$	$T_C = 25^{\circ}C$			10	μΑ
		$V_{CF} = 1 \text{ V, } I_{C} = 0.2 \text{ A}$	$T_C = 25^{\circ}C$	15	28	40	
		VCE = 1 V, IC = 0.2 A	$T_C = 125^{\circ}C$	8	18		
h	DC Current Gain	V _{CF} = 1 V, I _C = 1 A	$T_C = 25^{\circ}C$	4.0	6.4		
h _{FE}	DC Guileit Gaiii	VCE - I V, IC - I A	$T_C = 125^{\circ}C$	3.0	4.7		
		$V_{CE} = 2.5 \text{ V},$	$T_C = 25^{\circ}C$	12	20	30	
		I _C = 0.5 A	T _C = 125°C	6	12		
	Collector-Emitter Saturation Voltage	I _C = 0.2 A, I _B = 0.02 A	$T_C = 25^{\circ}C$		0.31	0.80	- V
			T _C = 125°C	7	0.54	1.10	
\/ (oot)		I _C = 0.4 A, I _B = 0.08 A	$T_C = 25^{\circ}C$	/i	0.15	0.60	
V _{CE} (sat)			$T_{\rm C} = 125^{\circ}{\rm C}$		0.23	1.00	
		I _C = 1 A, I _B = 0.2 A	$T_C = 25^{\circ}C$		0.40	1.50	
			T _C = 125°C		1.30	3.00	
	Base-Emitter Saturation Voltage	I _C = 0.4 A, I _B = 0.08 A	$T_C = 25^{\circ}C$		0.77	1.00	
			T _C = 125°C		0.60	0.90	V
V _{BE} (sat)			$T_C = 25^{\circ}C$		0.83	1.20	
		$I_C = 1 \text{ A}, I_B = 0.2 \text{ A}$ $T_C = 125^\circ$			0.70	1.00	
C _{ib}	Input Capacitance	$V_{EB} = 8 \text{ V, } I_{C} = 0, f = 1 \text{ MHz}$			385	500	pF
C _{ob}	Output Capacitance	V _{CB} = 10 V, I _E = 0, f = 1 MHz			60	100	pF
f _T	Current Gain Bandwidth Product	$I_C = 0.5 \text{ A}, V_{CE} = 10 \text{ V}$			11		MHz
	Diode Forward Voltage	I _F = 0.2 A	$T_C = 25^{\circ}C$		0.75	1.20	
			T _C = 125°C		0.59		
		I _F = 0.4 A	T _C = 25°C		0.80	1.30	V
			T _C = 125°C		0.64		
		I _F = 1 A	T _C = 25°C		0.90	1.50	

Electrical Characteristics

Values are at $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Conditions		Min	Тур.	Max.	Unit	
		I _F = 0.2 A			650			
Te.	Diode Froward Recovery Time (di/dt=10 A/μs)	I _F = 0.4 A			740		ns	
	Time (divate to A/µs)	I _F = 1 A			785			
		$I_C = 0.4 \text{ A}, I_{B1} = 80 \text{ mA},$	at 1 μs		7.2		V	
\/ (DCAT)	Dunamia Catumatian Valtana	V _{CC} = 300 V	at 3 µs		1.8			
VCE(DSAT)	Dynamic Saturation Voltage	$I_C = 1 \text{ A}, I_{B1} = 200 \text{ mA},$	at 1 μs		18.0			
		V _{CC} = 300 V	at 3 µs		6.0			
Resistive L	oad Switching (D.C < 10%, Pt	ulse Width = 20 s)			•			
4	Turn-On Time		$T_C = 25^{\circ}C$		175	350	ns	
t _{ON}	rum-on time	$I_C = 0.4 \text{ A}, I_{B1} = 80 \text{ mA},$	$T_{\rm C} = 125^{\circ}{\rm C}$		185			
	Turn-Off Time	$I_{B2} = 0.2 \text{ A}, V_{CC} = 300 \text{ V},$ $R_1 = 750 \Omega$	$T_C = 25^{\circ}C$		2.1	3.0	μs	
t _{OFF}	Turn-Oil Time		$T_{\rm C} = 125^{\circ}{\rm C}$		2.6			
. /	Turn On Time	I _C = 1 A, I _{B1} = 160 mA, I _{B2} = 160 mA,	$T_C = 25^{\circ}C$		240	450	ns	
t _{ON}	Turn-On Time		$T_{\rm C} = 125^{\circ}{\rm C}$		310			
	Turn-Off Time	$V_{CC} = 300 \text{ V},$	T _C = 25°C		3.7	5.0	μs	
t _{OFF}	Turri-On Time	$R_L = 300 \Omega$ $T_C = 12$	T _C = 125°C		4.5			
Inductive L	oad Switching (V _{CC} = 15 V)							
	Storage Time		T _C = 25°C		1.2	2.0	μs	
t _{STG}	Storage Time		T _C = 125°C		1.5			
4	Fall Time	$I_C = 0.4 \text{ A}, I_{B1} = 80 \text{ mA},$ $I_{B2} = 0.2 \text{ A}, V_Z = 300 \text{ V},$	$T_C = 25^{\circ}C$		90	200	no	
t _F	Fall fille	$I_{B2} = 0.2 \text{ A}, V_Z = 300 \text{ V},$ $I_C = 200 \text{ H}$	T _C = 125°C		65		ns	
4	Cross-Over Time		$T_C = 25^{\circ}C$		185	350	no	
t_{C}	Cross-Over Time		T _C = 125°C		145		ns	
	Storago Timo		$T_C = 25^{\circ}C$		3.30	4.50	μs	
t _{STG} Storage	Storage Time	$I_C = 0.8 \text{ A}, I_{B1} = 160 \text{ mA},$	T _C = 125°C		3.75			
t _F Fall Time	Fall Time	$I_{B2} = 160 \text{ mA},$	$T_C = 25^{\circ}C$		90	250	ns	
	I all fille	$V_{CC} = 300 \text{ V},$	T _C = 125°C		160			
t .	Cross-over Time	L _C = 200 H	$T_C = 25^{\circ}C$	<u> </u>	300	600	ne	
t _C	Cioss-over fille	T _C = 125°C			570	ns		

Typical Performance Characteristics

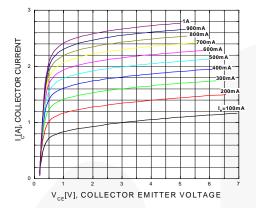


Figure 1. Static Characteristic

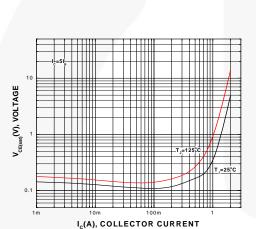


Figure 3. Collector-Emitter Saturation Voltage

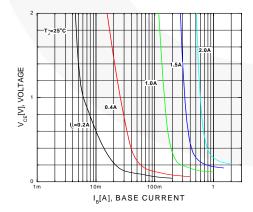


Figure 5. Typical Collector Saturation Voltage

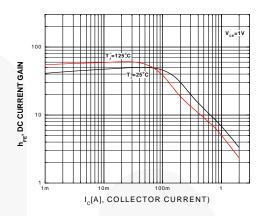


Figure 2. DC Current Gain

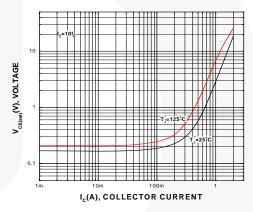


Figure 4. Collector-Emitter Saturation Voltage

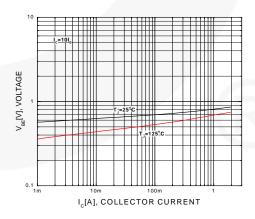


Figure 6. Base-Emitter Saturation Voltage

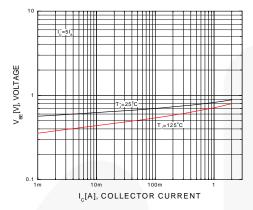


Figure 7. Base-Emitter Saturation Voltage

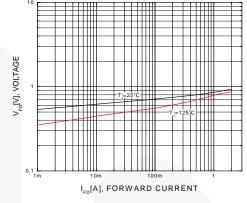


Figure 8. Diode Forward Voltage

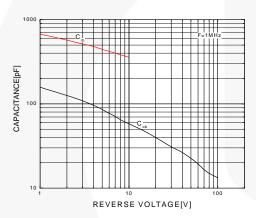


Figure 9. Collector Output Capacitance

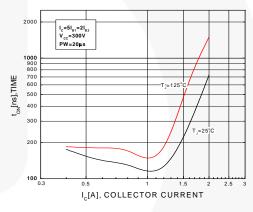


Figure 10. Resistive Switching Time, ton

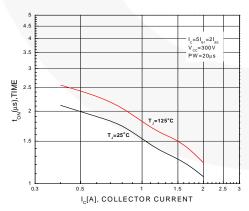


Figure 11. Resistive Switching Time, toff

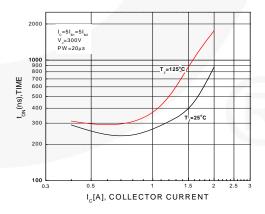


Figure 12. Resistive Switching Time, ton

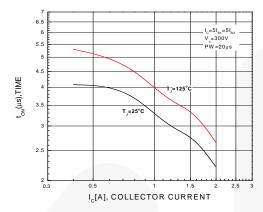
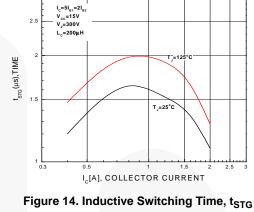


Figure 13. Resistive Switching Time, toff



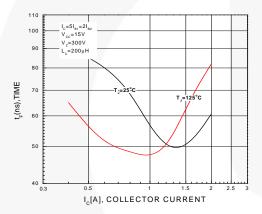


Figure 15. Inductive Switching Time, t_F

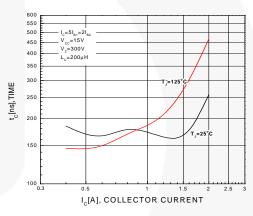


Figure 16. Inductive Switching Time, tc

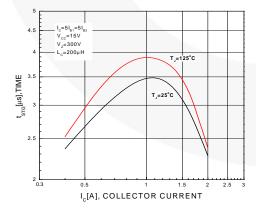


Figure 17. Inductive Switching Time, t_{STG}

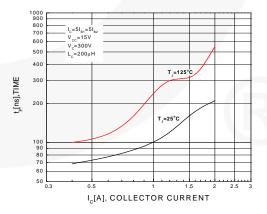


Figure 18. Inductive Switching Time, t_F

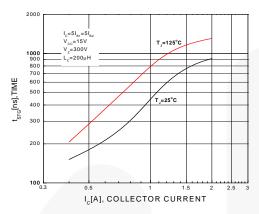


Figure 19. Inductive Switching Time, t_c

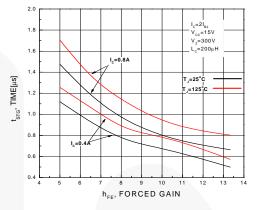


Figure 20. Inductive Switching Time, t_{STG}

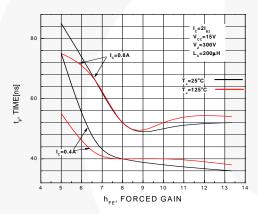


Figure 21. Inductive Switching Time, t_F

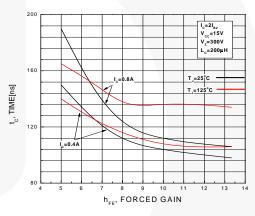


Figure 22. Inductive Switching Time, t_c

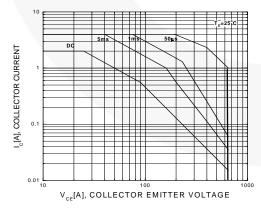


Figure 23. Forward Bias Safe Operating Area

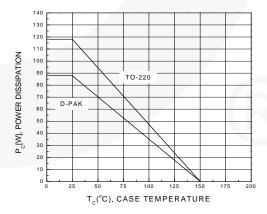


Figure 24. Power Derating

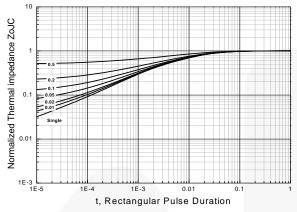


Figure 25. ZoJC, Transient Thermal Impedance (D-PAK)

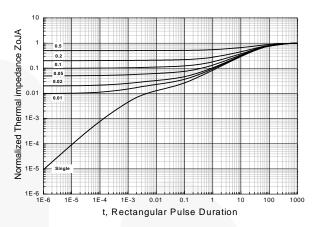


Figure 26. ZoJA, Transient Thermal Impedance (D-PAK)

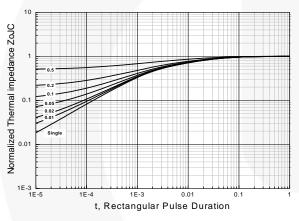


Figure 27. ZoJC, Transient Thermal Impedance (TO-220)

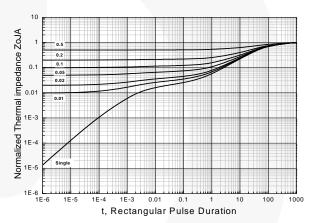


Figure 28. ZoJA, Transient Thermal Impedance (TO-220)

Physical Dimensions -5.55 MIN-_1.02 MAX (0.59)⊕ 0.25**M** A**M** C 4.57 LAND PATTERN_RECOMMENDATION 2.39 2.18 SEE NOTE D 4.32 MIN 0.45 MIN 10.41 SEE DETAIL A △ 0.10 B 0.51 NOTES: UNLESS OTHERWISE SPECIFIED A) THIS PACKAGE CONFORMS TO JEDEC, TO-252, ISSUE C, VARIATION AA. B) ALL DIMENSIONS ARE IN MILLIMETERS. C) DIMENSIONING AND TOLERANCING PER ASME 714.5M-2009. D) SUPPLIER DEPENDENT MOLD LOCKING HOLES OR CHAMFERED CORNERS OR EDGE PROTRUSION. E) PRESENCE OF TRIMMED CENTER LEAD IS OPTIONAL. F) DIMENSIONS ARE EXCLUSSIVE OF BURSS. GAGE PLANE 10. 1.78 1.40 0.127 MAX IS OPTIONAL. DIMENSIONS ARE EXCLUSSIVE OF BURSS, MOLD FLASH AND TIE BAR EXTRUSIONS. LAND PATTERN RECOMENDATION IS BASED ON IPC7351A STD T0228P991X239-3N. DRAWING NUMBER AND REVISION: MKT-T0252A03REV9. FAIRCHILD SEMICONDUCTOR. F) - SEATING PLANE (2.90)

Figure 29. TO-252 (D-PAK), MOLDED, 3-LEAD, OPTION AA & AB

DETAIL

Package drawings are provided as a service to customers considering Fairchild components. Drawings may change in any manner without notice. Please note the revision and/or date on the drawing and contact a Fairchild Semiconductor representative to verify or obtain the most recent revision. Package specifications do not expand the terms of Fairchild's worldwide terms and conditions, specifically the warranty therein, which covers Fairchild products.

Always visit Fairchild Semiconductor's online packaging area for the most recent package drawings: http://www.fairchildsemi.com/dwq/TO/TO252A03.pdf.

For current tape and reel specifications, visit Fairchild Semiconductor's online packaging area: http://www.fairchildsemi.com/packing_dwq/PKG-TO252A03.pdf.

G)

Physical Dimensions

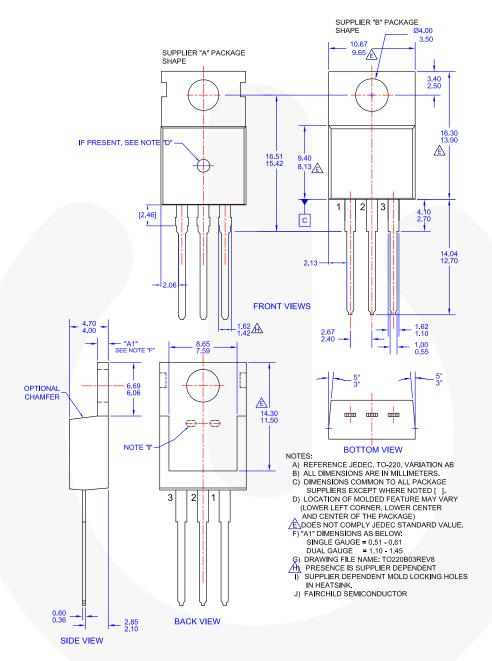


Figure 30. TO-220, MOLDED, 3LEAD, JEDEC VARIATION AB

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GTO™ IntelliMAX™ Current Transfer Logic™ DEUXPEED[®] ISOPLANAR™

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PRODUCT STATUS DEFINITIONS

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Datasheet Identification		Definition			
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